

# **HVB190S**

## Silicon Epitaxial Planar PIN Diode for High Frequency Attenuator

REJ03G0440-0100

(Previous: ADE-208-1597)

Rev.1.00 Dec 20, 2004

### **Features**

- Low capacitance. (C = 0.35 pF max)
- Low forward resistance. (rf =  $3.0 \Omega \text{ typ}$ )
- CMPAK package is suitable for high density surface mounting and high speed assembly.

### **Ordering Information**

| Type No. | Laser Mark | Package Code |  |
|----------|------------|--------------|--|
| HVB190S  | H9         | CMPAK        |  |

### **Pin Arrangement**





(Top View)

1. Cathode

2. Anode

3. Cathode Anode

# Absolute Maximum Ratings \*1

 $(Ta = 25^{\circ}C)$ 

| Item                 | Symbol         | Value       | Unit |
|----------------------|----------------|-------------|------|
| Reverse voltage      | V <sub>R</sub> | 50          | V    |
| Forward current      | I <sub>F</sub> | 50          | mA   |
| Power dissipation    | Pd             | 100         | mW   |
| Junction temperature | Tj             | 125         | °C   |
| Storage temperature  | Tstg           | −55 to +125 | °C   |

Note: 1. Absolute maximum ratings are described each unit separately.

## Electrical Characteristics\*1

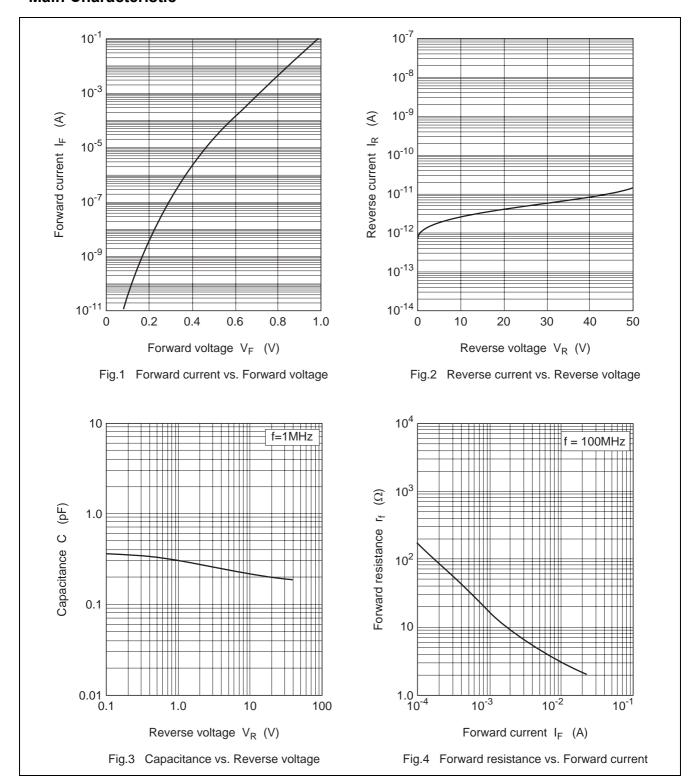
 $(Ta = 25^{\circ}C)$ 

| Item               | Symbol         | Min | Тур | Max  | Unit | Test Condition                       |
|--------------------|----------------|-----|-----|------|------|--------------------------------------|
| Forward voltage    | V <sub>F</sub> | _   | _   | 1.0  | V    | I <sub>F</sub> = 50 mA               |
| Reverse current    | I <sub>R</sub> | _   | _   | 100  | nA   | V <sub>R</sub> = 50 V                |
| Capacitance        | С              | _   | _   | 0.35 | pF   | V <sub>R</sub> = 50 V, f = 1 MHz     |
| Forward resistance | r <sub>f</sub> | _   | 3.0 | 5.0  | Ω    | I <sub>F</sub> = 10 mA, f = 100 MHz  |
| ESD-Capability *2  | _              | 200 | _   | _    | V    | C = 200 pF, Both forward and reverse |
|                    |                |     |     |      |      | direction 1 pulse                    |

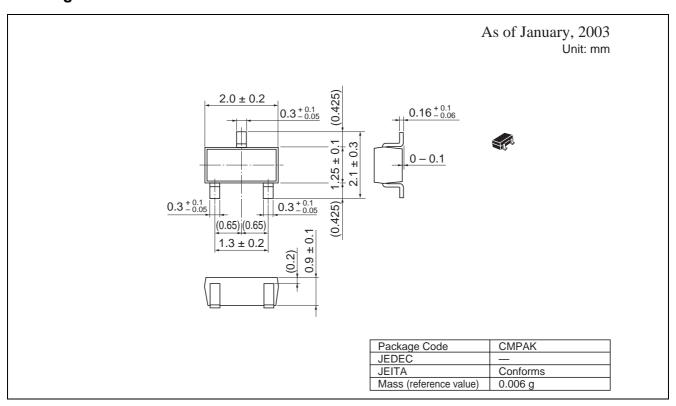
Notes: 1. Per one device.

2. Failure criterion;  $I_R \geq 200 \ nA$  at  $V_R$  = 50 V

### **Main Characteristic**



### **Package Dimensions**



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